

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	)	
	)	
Sung-nam LEE et al.	)	Group Art Unit: Unknown
	)	
Application No.: Unknown	)	Examiner: Unknown
	)	
Filed: February 6, 2001	)	
	)	
For: NITRIDE SEMICONDUCTOR	)	
LIGHT EMITTING DEVICE	)	

**PRELIMINARY AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to examination on the merits and calculation of claim fees, kindly amend the  
above-captioned application as follows:

**IN THE CLAIMS:**

Claim 14, line 1, delete "or claim 13."

Claim 15, line 1, delete "or claim 13."

Kindly add the following new claims 14 and 15.

--14. The nitride semiconductor light emitting device of claim 13, wherein the  
active layer is a III-V group nitride compound semiconductor layer having a multi-quantum  
well structure.

15. The nitride semiconductor light emitting device of claim 13, wherein the n-type clad layer has a thickness between  $0.5\ \mu\text{m}$  and  $1.7\ \mu\text{m}$ . --

REMARKS

The above changes are designed to remove multiple dependency to avoid the additional fee therefor and to incorporate by reference the priority document. Prompt and favorable action on the merits are respectfully requested.

Respectfully submitted,

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By: 

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